BLC8G27LS-100AV

Power LDMOS transistor Rev. 1 — 25 February 2014

Objective data sheet

1. **Product profile**

1.1 General description

100 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2490 MHz to 2690 MHz.

Table 1. **Typical performance**

Typical RF performance at $T_{\text{case}} = 25 \,^{\circ}\text{C}$ in the Doherty demo board.

Test signal	f	V_{DS}	$P_{L(AV)}$	Gp	η_{D}	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2520 to 2620	28	17	15.5	45	-30 [<u>1]</u>

^[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

RF power amplifier for LTE base stations and multi carrier applications in the 2490 MHz to 2690 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)		5 4 0 0	4.5
2	drain2 (peak)			1, 5
3	gate1 (main)			3
4	gate2 (peak)		7	7
5	video decoupling (main)			* -
6	video decoupling (peak)		3 4	2, 6
7	source	<u>[1]</u>		aaa-007731

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLC8G27LS-100AV	-	plastic earless flanged cavity package; 6 leads	SOT1275-1	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage			-	65	V
V_{GS}	gate-source voltage			-0.5	+13	V
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature		[1]		225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 17 W	<tbd></tbd>	K/W

6. Characteristics

<tbd>

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7. Package outline

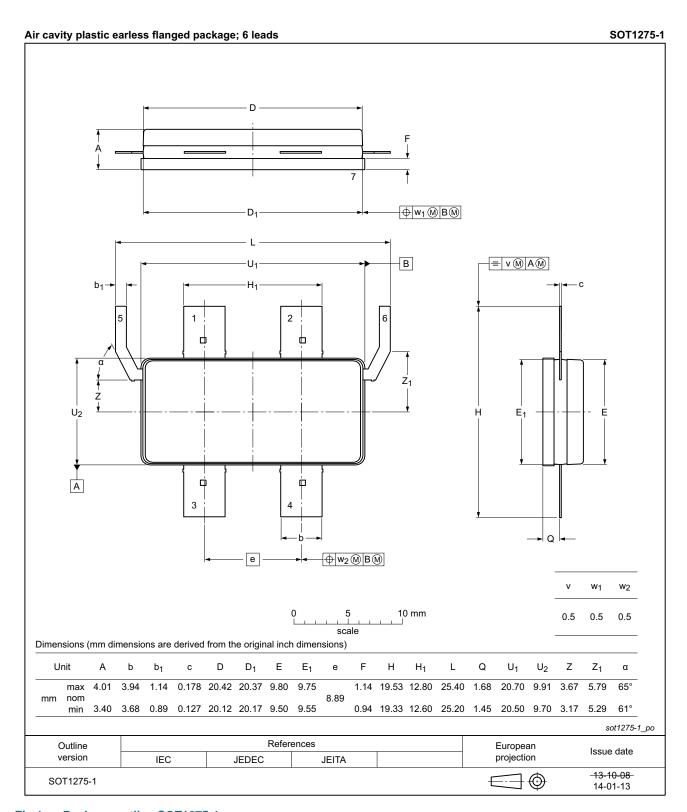


Fig 1. Package outline SOT1275-1

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8. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

9. Abbreviations

Table 6. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-100AV v.1	20140225	Objective data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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